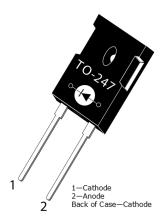


# MSC030SDA170B Zero Recovery Silicon Carbide Schottky Diode

#### 1 Product Overview

This section shows the product overview for the MSC030SDA170B device.



#### 1.1 Features

The following are key features of the MSC030SDA170B device:

- No reverse recovery
- Low forward voltage
- Low leakage current
- Avalanche energy rated
- RoHS compliant

#### 1.2 Benefits

The following are benefits of the MSC030SDA170B device:

- High switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

## 1.3 Applications

The MSC030SDA170B device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
  - Switch-mode power supply
  - Inverters/converters
  - Motor controllers
- Freewheeling diode
  - Switch-mode power supply
  - Inverters/converters
- Snubber/clamp diode



# **2** Device Specifications

This section details the device specifications for the MSC030SDA170B device.

## 2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the MSC030SDA170B device. All ratings:  $T_c$  = 25 °C unless otherwise specified.

**Table 1 • Absolute Maximum Ratings** 

Symbol	Parameter		Ratings	Unit
VR	Maximum DC reverse voltage		1700	V
VRRM	Maximum peak repetitive reverse voltage		1700	=
V <sub>RWM</sub>	Maximum working peak reverse voltage		1700	=
l <sub>F</sub>	Maximum DC forward current	Tc = 25 °C	82	Α
		Tc = 135 °C	38	=
		Tc = 145 °C	31	_
IFRM	Repetitive peak forward surge current ( $T_c$ = 25 °C, $t_p$ = 8.3 ms, half sine wave)		116	_
IFSM	Non-repetitive forward surge current ( $T_c$ = 25 °C, $t_p$ = 8.3 ms, half sine wave)		353	_
Ptot	Power dissipation	Tc = 25 °C	429	W
		Tc = 110 °C	186	_
Tı, Tstg	Operating junction and storage temperature range		-55 to 175	°C
TL	Lead temperature for 10 seconds		300	_
Eas	Single pulse avalanche energy (starting $T_J$ = 25 °C, L = 0.22 mH, peak $I_L$ = 30 A)		100	mJ

The following table shows the thermal and mechanical characteristics of the MSC050SDA170B device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min	Тур	Max	Unit
Rejc	Junction-to-case thermal resistance		0.24	0.35	°C/W
Wt	Package weight		0.22		OZ
			6.2		g
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m



## 2.2 Electrical Performance

The following table shows the static characteristics of the MSC030SDA170B device.

**Table 3 • Static Characteristics** 

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
VF	Forward voltage	I <sub>F</sub> = 30 A, T <sub>J</sub> = 25 °C		1.5	1.8	V
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 175 °C		2.25		=
Irm	Reverse leakage current	V <sub>R</sub> = 1700 V, T <sub>J</sub> = 25 °C		4	200	μΑ
		V <sub>R</sub> = 1700 V, T <sub>J</sub> = 175 °C		125		=
<b>Q</b> c	Total capacitive charge	V <sub>R</sub> = 900 V, T <sub>J</sub> = 25 °C		230		nC
Cı	Junction capacitance	V <sub>R</sub> = 1 V, T <sub>J</sub> = 25 °C, f = 1 MHz		2070		pF
	Junction capacitance	$V_R = 600 \text{ V}, T_J = 25 \text{ °C}, f = 1 \text{ MHz}$		167		=
	Junction capacitance	V <sub>R</sub> = 900 V, T <sub>J</sub> = 25 °C, f = 1 MHz		138		-

#### 2.3 Performance Curves

This section shows the typical performance curves for the MSC030SDA170B device.

Figure 1 • Maximum Transient Thermal Impedance

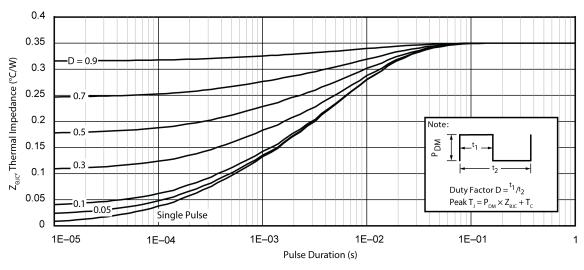




Figure 2 • Forward Current vs. Forward Voltage

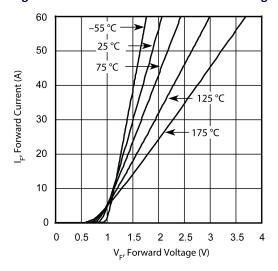


Figure 4 • Max. Power Dissipation vs. Case Temp.

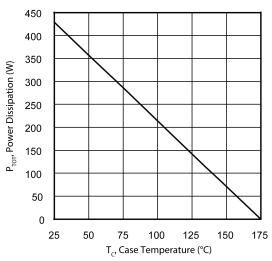


Figure 6 • Total Capacitive Charge vs. Reverse Voltage

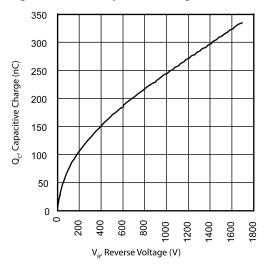


Figure 3 • Max. Forward Current vs. Case Temp.

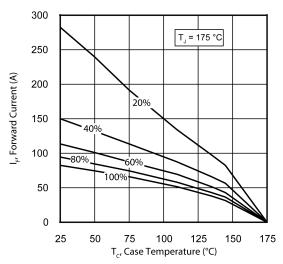


Figure 5 • Reverse Current vs. Reverse Voltage

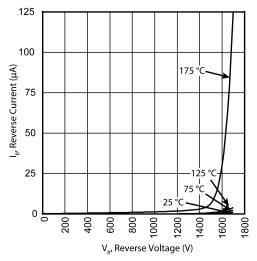
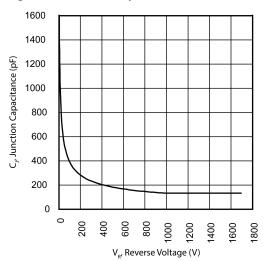


Figure 7 • Junction Capacitance vs. Reverse Voltage





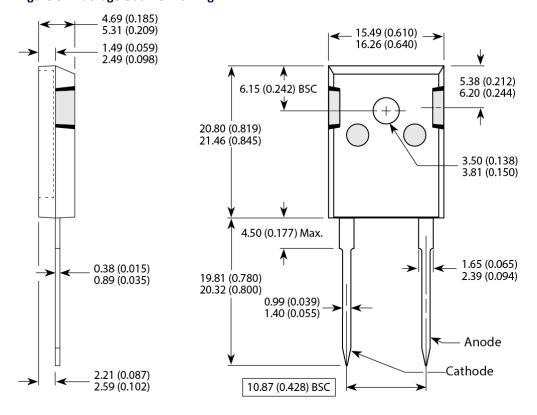
# **3** Package Specification

This section outlines the package specification for the MSC030SDA170B device.

## 3.1 Package Outline Drawing

This section details the TO-247 package drawing of the MSC030SDA170B device. Dimensions are in millimeters and (inches).

Figure 8 • Package Outline Drawing







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